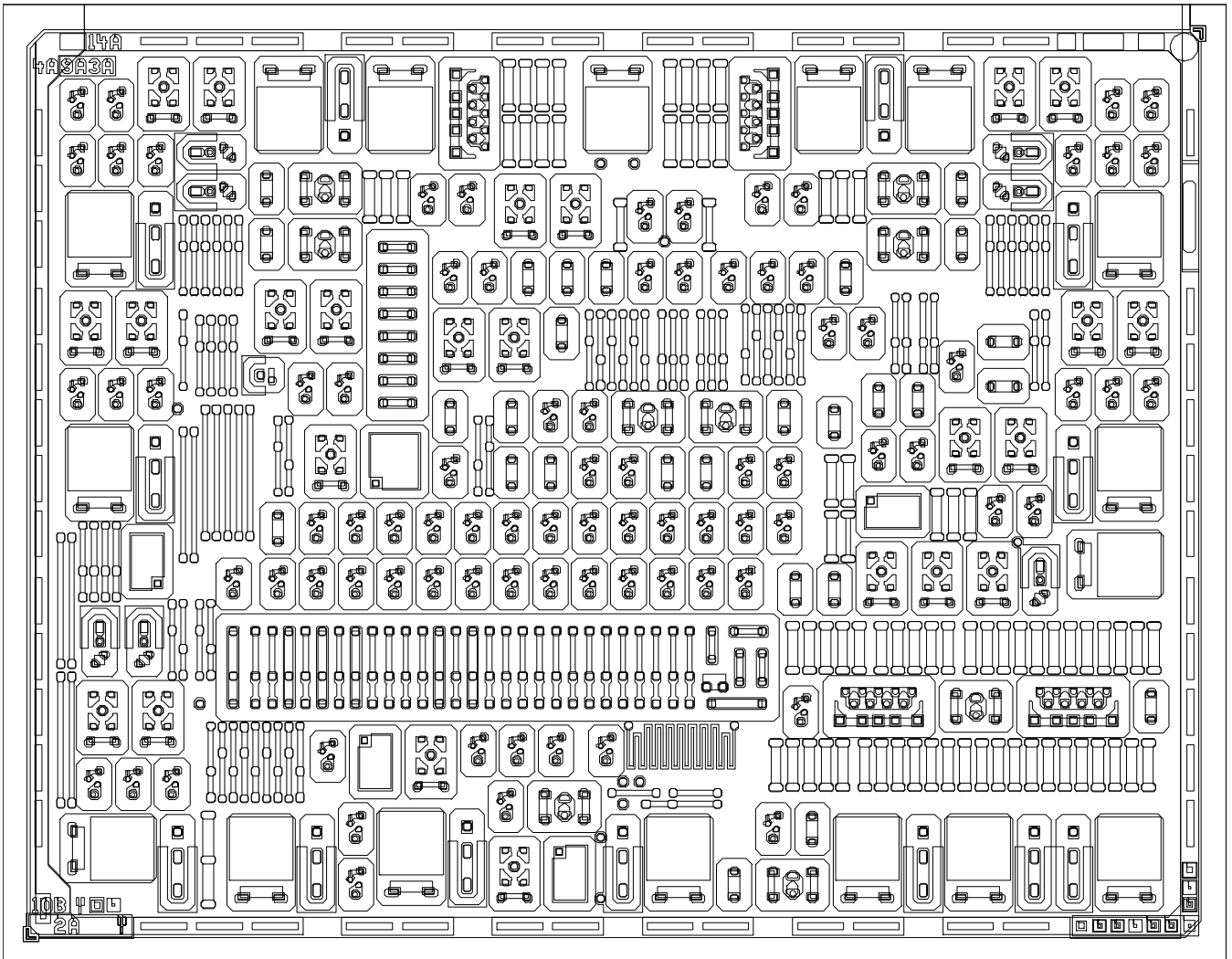


Special Features: - improved V_{BE} -matching - SiCr Resistors

Die Size	app. 2.4 x 1.8 mm ²	36 k Ω Resistor (SiCr)	11
V_{max}	36 V	12 k Ω Resistor (SiCr)	65
Bonding Pads	17	10 k Ω Resistor (SiCr)	1
50 mA NPN Transistor	4	8 k Ω Resistor (SiCr)	1
10 mA NPN Transistor	9	6 k Ω Resistor (SiCr)	138
5 mA NPN Transistor	92	4 pF Capacitor	1
1 mA PNP Transistor lateral	24	3 pF Capacitor	4
1 mA PNP Transistor vertical	1	Crossunder	51
1.2 k Ω Resistor (base diffused)	22	Total Capacitance	16 pF
0.6 k Ω Resistor (base diffused)	22	Total Resistance (SiCr)	2.5 M Ω
460 k Ω Resistor (SiCr)	1	Total Resistance (diffused)	39.6 k Ω



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